

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current V _{GS} = -4.5V (Note 7)	Steady State	T _C = +25°C T _C = +70°C	I _D	-89 -70	A
Continuous Drain Current V _{GS} = -4.5V (Note 6)	Steady State	T _A = +25°C T _A = +70°C	I _D	-19 -15	A
Pulsed Drain Current (380µs pulse, duty cycle = 1%)			I _{DM}	-100	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-2.5	A
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	-27	A
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	35	mJ

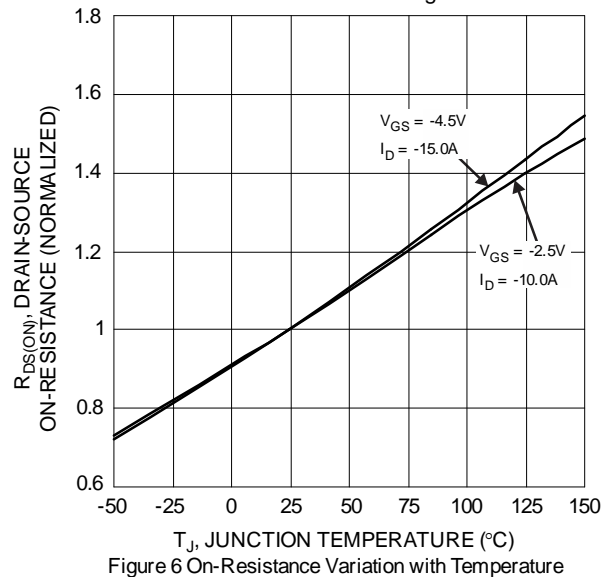
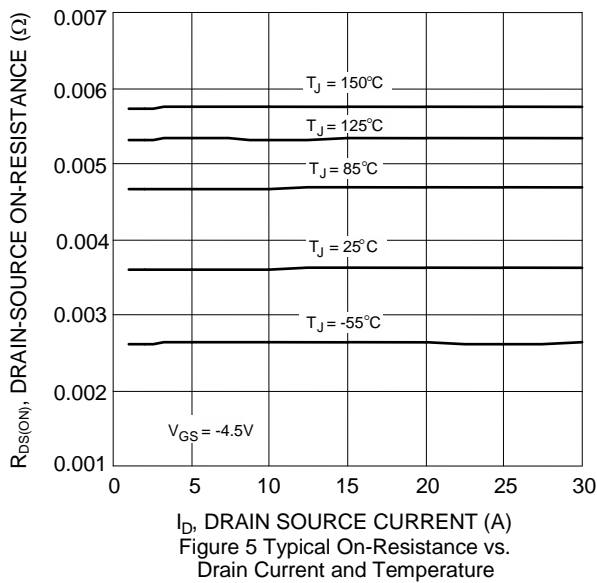
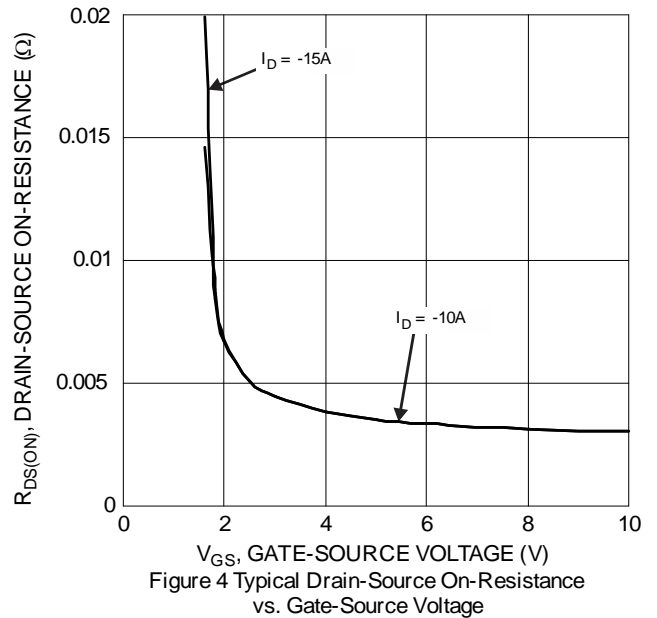
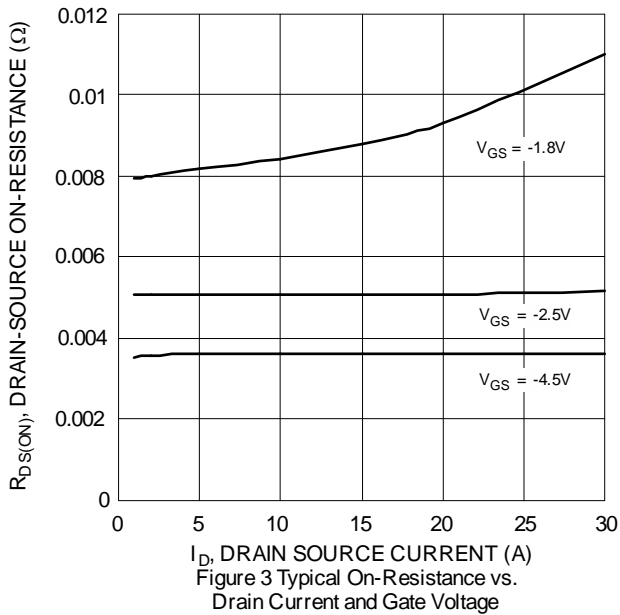
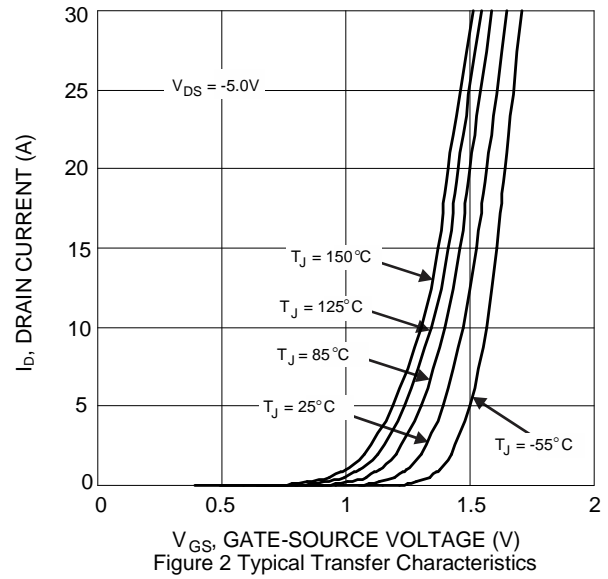
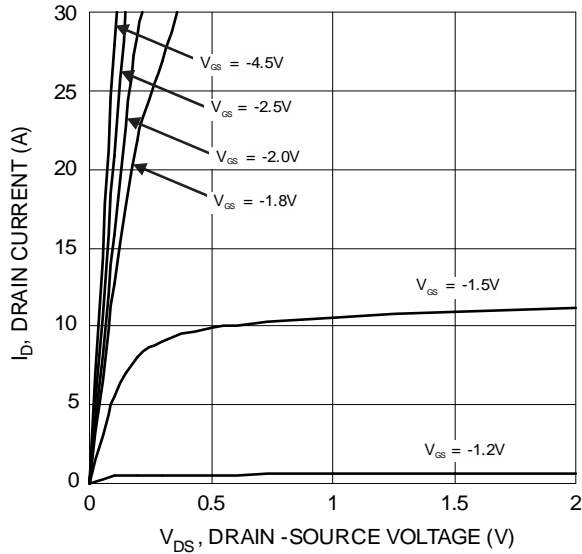
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

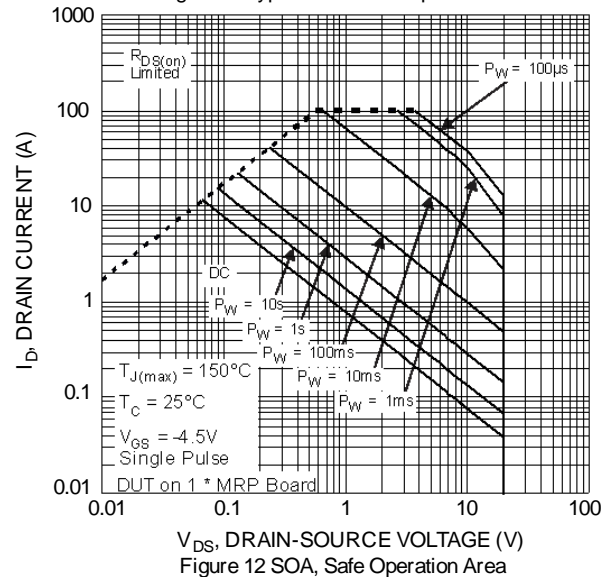
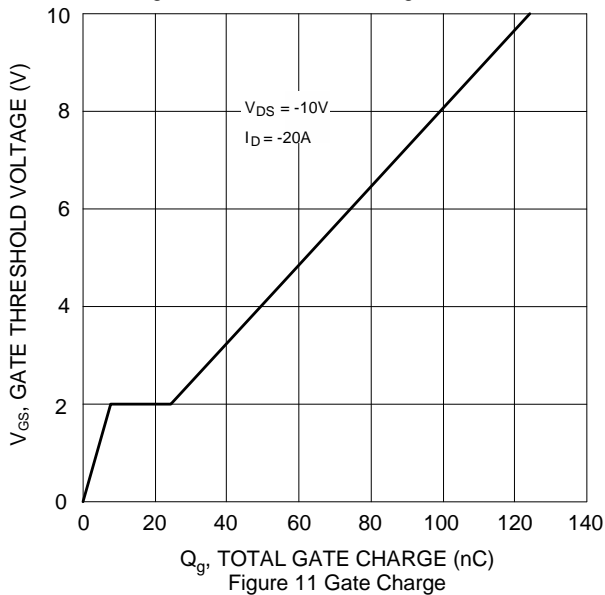
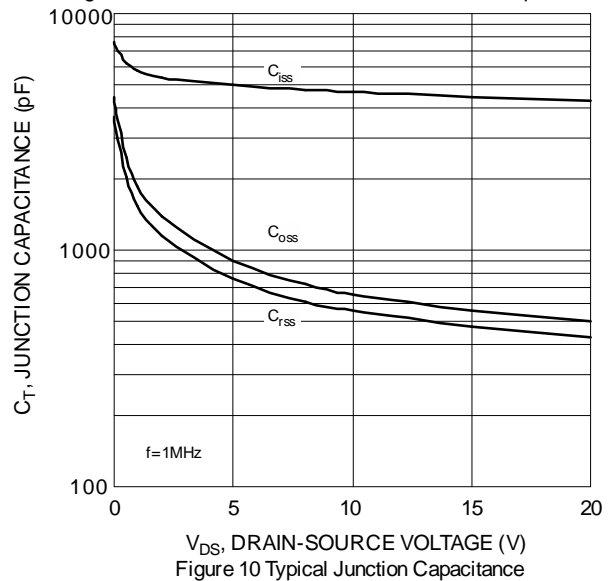
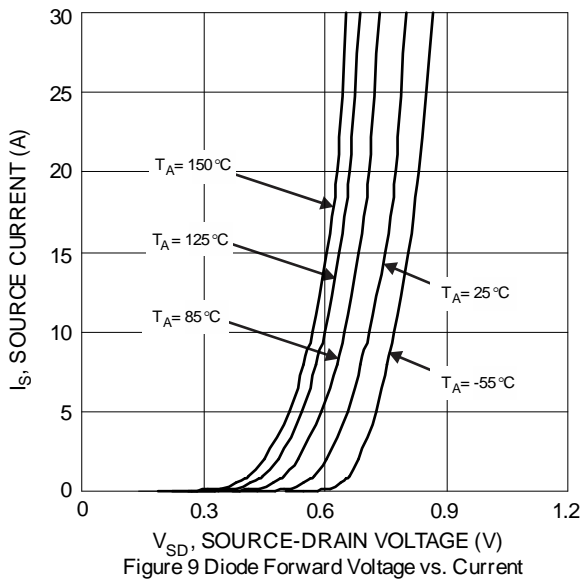
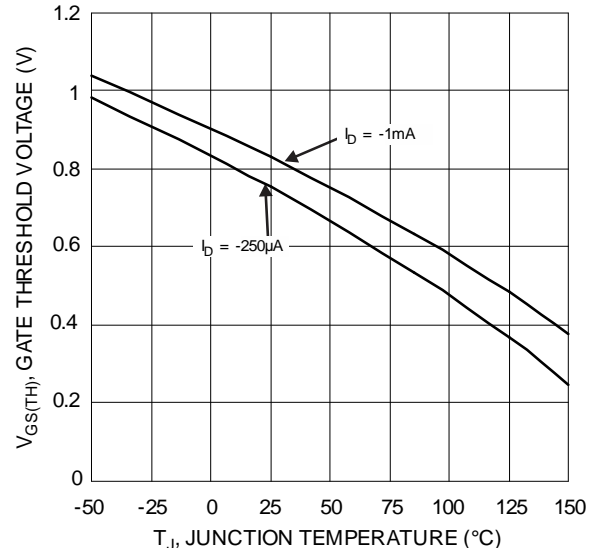
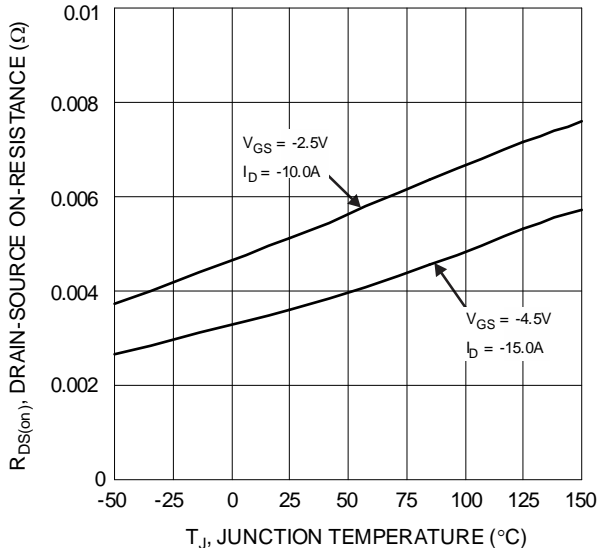
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	128	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	57	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	48	W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	2.6	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

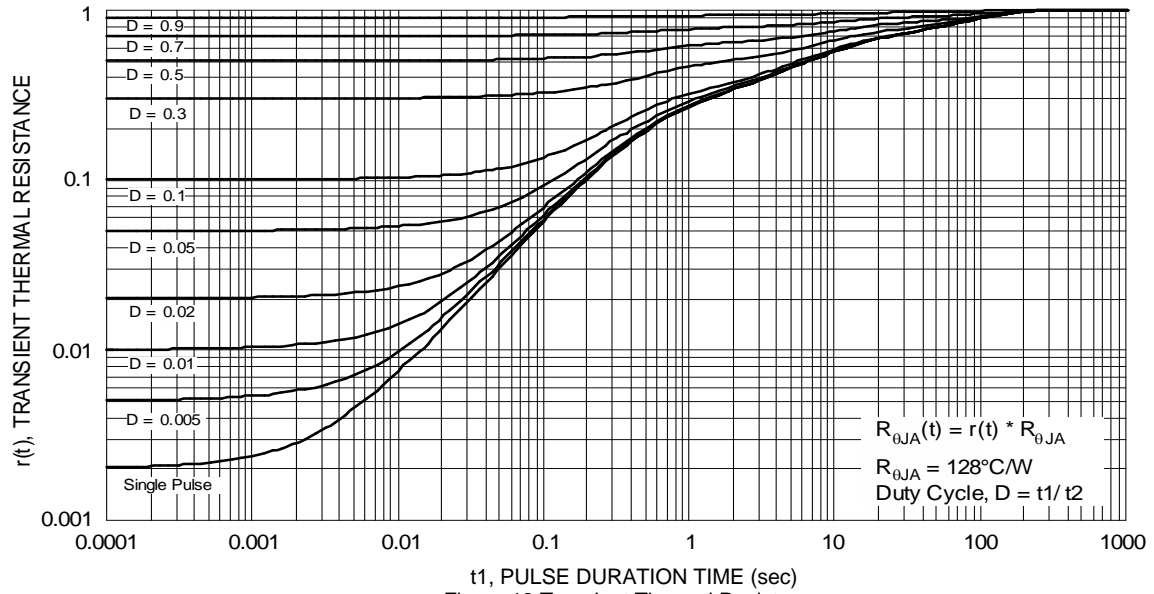
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-0.3	-0.7	-0.9	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.5	4.0	mΩ	V _{GS} = -4.5V, I _D = -15A
		—	5.4	6.5		V _{GS} = -2.5V, I _D = -10A
		—	8.0	14		V _{GS} = -1.8V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -10A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	4,670	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	650	—		
Reverse Transfer Capacitance	C _{rss}	—	550	—		
Gate Resistance	R _G	—	3.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	55	—	nC	V _{DD} = -10V, I _D = -20A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	125	—		
Gate-Source Charge	Q _{gs}	—	7.8	—		
Gate-Drain Charge	Q _{gd}	—	16.5	—		
Turn-On Delay Time	t _{D(ON)}	—	9.5	—	ns	V _{GS} = -4.5V, V _{DD} = -10V, R _G = 1Ω, R _G = 1Ω, I _D = -10A
Turn-On Rise Time	t _r	—	10.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	115	—		
Turn-Off Fall Time	t _f	—	85	—		
Reverse Recovery Time	t _{RR}	—	25	—	ns	I _F = -10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	14	—	nC	I _F = -10A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



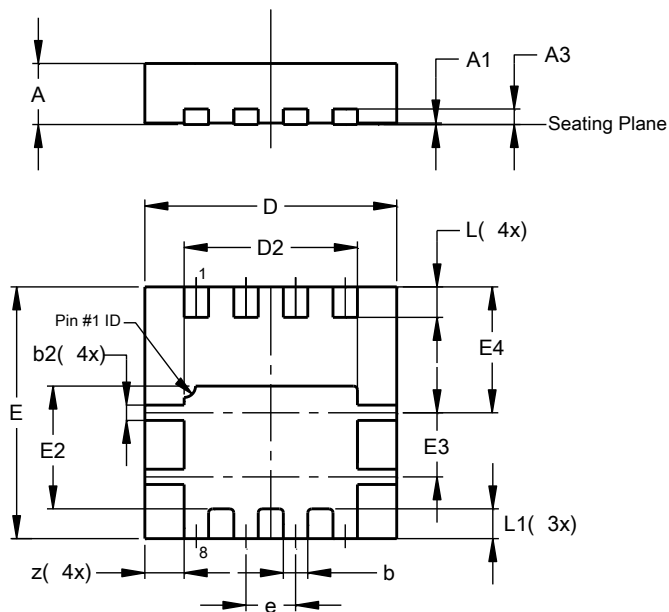




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

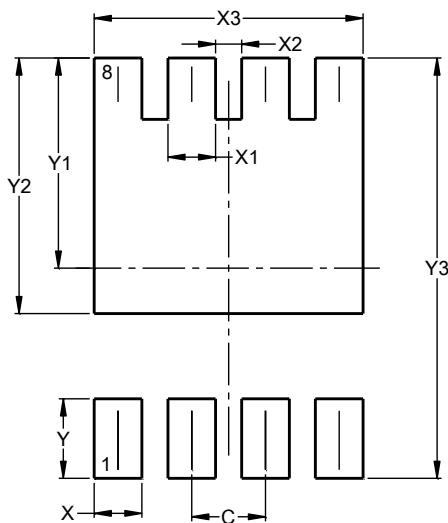


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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